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LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT Applicant(s): M.A. Shbib et al.

Case: 41

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Serial No.: Filing Date: TDA 10/7/9/95 November 21, 2003

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CC 1. 6,461,902 10/08/02 Xu et al. 438/163 FOREIGN PATENT DOCUMENTS	12CTO2	UKE STATE	ALCIN I		, Oroup.	2012	
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